

EXHIBIT H



WAFER FAB GROUP

2001 BUDGET

**2001–2003
3-YEAR PLAN**

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Advanced Micro Devices, Inc.

3 Year Plan Commentary

Wafer Fabrication Group

December, 2000

Wafer Fabrication Group

3 Year Plan Commentary

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1. Executive Summary

Overview: Mission, Capabilities, Current Situation and Summary of WFG's Strategy to Win

The mission of the Wafer Fabrication Group (WFG) is to provide wafer production support to the Computation Products Group (CPG) and the Memory Group (MG) that meets their performance, volume, cost, quality and service requirements.

The WFG consists of the Fab 14/15 and Fab 25 in Austin, Texas, Fujitsu/AMD Joint Venture (FASL I, II, III, Iwate and GMD, in Gresham, Oregon), AMD Saxony Manufacturing GmbH (Fab 30, Dresden, Germany) and external suppliers (Epson, Motorola, Sony, TSMC, UMC and IBM).

The most important priorities facing wafer fabrication in 2001 will be the continued successful ramp of Fab 30, while preparing the next-generation 0.13 μ HiP7 technology for Athlon and Hammer products; the supply of Athlon product (mostly Duron) from Fab 25 at the proper speed mix, while supporting the transistor development to increase the frequency performance to ~ 2 Ghz by yearend and enabling a low power mobile part in 1Q2001; and, build out of sufficient Flash capacity (JV3, GMD) to stabilize/grow market share, while ramping into production the next-generation CS59 (0.18 μ) technology for high density NOR Flash products.

One of the most critical strategic issues is the definition of a capacity plan that matches the technology and volume requirements of CPG. The microprocessor unit demand fully utilizes Fabs 25 and 30 through 2001 and most of 2002, but is significantly short of full utilization of Fab 25 (<50%) in 2003.

The plan capacity had been built around a strategy to convert Fab 25 to copper/0.13 μ technology to provide sufficient volume capability through 2003 and beyond. However, this plan will be abandoned in favor of converting Fab 25 to Flash production, starting in 2002. As a result, microprocessors unit volume requirements that cannot be satisfied by Fab 30 alone will be met by external foundries, starting in 2002. Finally, the need for additional capacity beyond the three year horizon is expected to be met by a new facility (Fab 35), currently in the planning phase.

Wafer fabrication at AMD has advanced to the level that few, if any, in this industry have achieved. Fab 25 performs at high volumes and high yields, while exhibiting extraordinary flexibility to move the process to the "edge" of process capability, with good control. On-line process development, alongside volume production, enables more rapid technology and product performance advancements, and has played a major role in AMD's ability to achieve the edge over Intel. This capability has been transferred to Fab 30, with similar results already being achieved.

Combining high volume, cost effective manufacturing, with heavy development focus, and outstanding manufacturing control, has become a hallmark of AMD wafer fabrication.

1.1 **Fab 14/15**

Fab 14/15 mission is to support AMD's business segments requiring a complex mix of CMOS Logic, High Density Programmable Logic, Non-Volatile Memory, and BiPolar. Internal customers supported by Fab 14/15 include Network Products Division (NPD), Embedded Products Division (EPD), and Non-Volatile Memory Division (NVD). External customers include Lattice and Legerity. Based on current demands from these customers, Fab 14/15 is at or near capacity for the next 3 years.

The 2001 focus will be the ramp of the Bipolar HV-4 and the development and initial production ramp of the Bipolar HV-7 technologies for Legerity.

Fab 14/15 will transition from 56% of its wafer out volume for internal customers to 22% by 2003. Fab 14/15 will continue efforts in wafer cost reductions and quality improvements in order to remain competitive.

1.2 **Fab 25**

Fab 25 is designed to provide state of the art microprocessors for desktop, mobile, and embedded computing solutions. In addition to its primary thrust in the CPG, Fab 25 also supports logic products for EPD. Output has been ramped to full capacity at 5000 outs/week. The technology transition to 0.18 micron will be complete in 1Q2001. Critical advanced transistor development for Fab 25 and Fab 30 is supported within the Fab 25 organization, with much of this material requiring expedited cycle times. Microprocessor ASP erosion drives continuing emphasis on defect density reduction activities to reduce die cost.

As stated earlier, Fab 25 has been preparing for the introduction of copper/0.13 μ technology, which is the basis for this budget. However, since the three year microprocessor demand will not sufficiently utilize the installed capacity, Fab 25 will convert to Flash (0.18 μ) production, starting in 2002. Detailed plans will be developed in 1Q2001.

1.3 **Fab 30**

The mission of fab 30 is to be AMD's leading technology high volume microprocessor production fab. Fab 30 supports leading edge microprocessors for CMD/TMD currently using 0.18 micron copper technology, transitioning to 0.13 micron copper technology by 2002. Base technologies are developed in the AMD/Motorola Alliance, with auxiliary development occurring in the SDC. Transistor developments are supported in Fab 30 in close conjunction with transistor development in Fab 25.

Keys to success is the ability to rapidly insert the leading edge technology into production while ramping the fab to full capacity and maintaining the highest yields possible. After achieving initial production output in 2000, Fab 30 will ramp to 140K wafers out in 2001, 220K wafers out in 2002, and 260K wafer outs in 2003.

Primary focus for 2001 will be to execute flawlessly in meeting the production ramp and the technology transition to 0.13 micron. Additional focus must be placed on keeping Athlon competitive in 2001, reaching 2 ghz by 4Q2001 (key strategies are transistor development and Athlon on HiP7), and getting K8 into production (key strategy is implementing HiP7 SOI technology).

The primary competitor to AMD and hence Fab 30 in microprocessors is Intel. Since Intel has much more capital to invest in capacity and development, many more engineers employed in these tasks, and multiple production fabs available for capacity, other key strategies are flexibility and speed. Fab 30 is being equipped "just in time", i.e. equipment is being purchased at the last possible moment to enable the most advanced equipment to be selected and installed. Systems have been developed and deployed to allow the process technology in Fab 30 to be quickly and frequently changed as technology is developed and learned. Significant investments in factory systems, in-line process control, advanced process control, and, of course, training to be able to use these systems are key elements of the "flexibility and speed" strategy.

1.4 Foundry Services

The mission of Foundry Services is to provide an external manufacturing supply of wafers to those divisions that are not fully supported with internal capacity. Capacity limitations, technological availability, and strategic priority drive the requirement for external support. Historically, AMD's use of foundries was driven by opportunistic capacity not met by internal fabrication. Today, foundries are being positioned to provide capacity such that it may not be necessary to supply 100% of the volume needs internally. This should enable more effective utilization of existing factories, while avoiding capital expenditures.

The role of the Foundry Services organization is to manage the wafer foundry programs from technical feasibility through mature production. In the production phase, Foundry Services is responsible for the schedule and delivery of products from the foundries, while ensuring conformance to quality requirements and cost targets.

The foundry network consists of:

Epson. Epson will continue production through the year 2001 at the Fujimi Japan production facility on five and six-inch wafer processes in support of the EPD product requirements.

Foundry for Athlon. This foundry will provide 0.13-micron microprocessor capacity starting in the year 2002 for the CPG. The purpose is to provide an early source of Athlon product on 0.13 μ technology to augment the 0.13 μ capacity from Fab 30.

Motorola. Motorola C4 evaporated bump manufacturing capacity will continue to be utilized at the Austin facility until the internal AMD bump capacity can support the total bump requirement. Bump

production at Motorola is planned to continue through 2Q2002, with volumes projected to range between 15K – 25K per quarter.

Sony Semiconductor Company of America. Sony will continue production at its San Antonio production facility through the year 2001 in support of low volume EPD product requirements.

Taiwan Semiconductor Manufacturing Company (TSMC), Taiwan. TSMC will continue production in support of low volume NPD product requirements.

United Microelectronics Corporation (UMC), Taiwan. UMC will be used to support NPD, EPD and the Chip Set (PPD) requirements.

1.5 **Fab 35**

Long-range CPG projections indicate that additional capacity will be needed in the 2004-2005 timeframe. This will be a 300mm factory, and will require substantial advance planning to execute properly.

Fab 35 will likely startup as 100 nanometer technology and will employ the newest manufacturing technology. The plant will be highly automated and will rely heavily on Advanced Process Control and manufacturing systems currently under development in WFG.

This project will undoubtedly require a partner, to share the initial investment and absorb the capacity. Partner options are numerous but priority must be given to a technology partner. Location options are many, depending on partner; strong preference is to locate Fab 35 in Austin area, to capitalize on existing manufacturing know-how and proximity to the product line.

1.6 **Fujitsu AMD Semiconductor, Ltd. (FASL) I, II, III**

The mission of FASL is to be the cost effective volume producer of AMD and Fujitsu jointly developed flash products in support of Memory Group.

The FASL strategy is to leverage process technology, innovative products and manufacturing technology enabling AMD and Fujitsu to be the leaders in the flash memory business. FASL will support the entire technology portfolio of products...floating gate (CS59S) for high speed NOR, NROM (CS99) for low cost NOR, and NAND (CS59N) for mass storage applications.

FASL I is the volume Fab for 0.35 micron NOR products and is operating at full capacity of 7500 production starts per week. Over time, a portion of the volume will be converted to CS-99 for low-density products.

FASL II is nearing full volume (6000 wafer starts per week) of predominantly CS-49S NOR technology and a small volume of CS-49N NAND technology. Development work is currently underway for both the CS-99 NROM technology and CS-59S floating gate technology. When development is complete, the CS-

3.2 Advanced CMOS Logic Support - Fab 25/Fab 30

Wafers Out (k) 200mm

DIVISION

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>
CMD/TMD	85.9	88.1	96.8	94.6	365.4	426.2	364.6
EPD	1.8	2.9	3.7	3.9	12.3	17.5	15.1
LATTICE	0.1	0.0	0.0	0.0	0.1	0.0	0.0
TOTAL	87.8	91.0	100.5	98.5	377.8	443.7	379.7

TECHNOLOGY

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>
CS-34 (3LM, 0.35u)	1.5	1.6	2.1	2.0	7.2	6.2	4.6
CS-44E72 (5LM, 0.25u)	5.4	0.7	0.6	0.6	7.3	1.9	1.2
CS-50/H6 (6LM, 0.18u)	54.8	56.1	59.4	59.1	229.4	188.7	11.9
EE7 (3LM, 0.25u)	0.1	0.0	0.0	0.0	0.1	0.0	0.0
HiP7L-bulk (7LM, 0.13u)	0.0	0.0	0.0	0.0	0.0	34.4	105.3
Fab 25 TOTAL	61.8	58.4	62.1	61.7	244.0	231.2	123.0
HiP6L (6LM, 0.18u)	26.0	32.6	38.4	36.8	133.8	107.4	0.0
HiP68 (9LM, 0.13u)	0.0	0.0	0.0	0.0	0.0	11.8	0.0
HiP7L-bulk (7LM, 0.13u)	0.0	0.0	0.0	0.0	0.0	59.7	66.6
HiP7L-SOI (9LM, 0.13u)	0.0	0.0	0.0	0.0	0.0	33.7	190.1
Fab 30 TOTAL	26.0	32.6	38.4	36.8	133.8	212.6	256.7
TOTAL							
Fab 25 Capacity Utilization	98%	93%	99%	99%	97%	95%	51%
Fab 30 Capacity Utilization	100%	100%	100%	100%	100%	100%	100%

3.3 Foundries Support

DIVISION

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>
CMD/TMD	0.0	0.0	0.0	0.0	0.0	16.9	0.0
EPD	1.0	1.4	1.5	1.6	5.5	7.2	9.3
NPD	0.7	1.1	1.1	1.2	4.1	4.9	8.0
PPD	9.4	11.4	10.0	6.7	37.5	31.4	105.8
TOTAL	11.1	13.9	12.6	9.5	47.1	60.4	123.1

TECHNOLOGY

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>
0.13u	0.0	0.0	0.0	0.0	0.0	16.9	0.0
0.18u 1P5M	0.0	0.0	0.0	0.2	0.2	6.4	4.8
0.18u 1P6M	0.0	0.0	0.0	0.0	0.0	5.2	71.8
0.18u 5LM	0.0	0.0	0.0	0.0	0.0	0.4	0.9
0.18u 6LM	0.0	0.0	0.0	0.0	0.0	0.6	3.8
0.25u 1P4M	9.5	10.2	8.8	6.0	34.5	24.6	36.0
0.25u 1P5M	0.0	1.3	1.6	1.4	4.3	0.7	0.5
0.32u 1P3M	0.2	0.3	0.4	0.5	1.4	1.7	1.7
0.35u 1P3M	0.8	1.5	1.4	1.1	4.8	3.4	3.2
0.35u 2P3M	0.0	0.1	0.1	0.1	0.3	0.5	0.4
IMOX2	0.3	0.2	0.0	0.0	0.5	0.0	0.0
IMOX2S	0.2	0.1	0.0	0.0	0.3	0.0	0.0
LS	0.0	0.1	0.2	0.1	0.4	0.0	0.0
SMS12	0.0	0.0	0.0	0.0	0.0	0.0	0.0
SMSSDL	0.1	0.1	0.1	0.1	0.4	0.0	0.0
TOTAL	11.1	13.9	12.6	9.5	47.1	60.4	123.1

CAPACITY UTILIZATON	100%	100%	100%	100%	100%	100%	100%
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FOUNDRIES

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>2002</u>	<u>2003</u>
EPSON	0.1	0.1	0.1	0.1	0.4	0.0	0.0
FOUNDRY #1	0.0	0.0	0.0	0.0	0.0	16.9	0.0
SONY	0.6	0.4	0.2	0.1	1.3	0.0	0.0
TSMC	0.0	0.1	0.1	0.1	0.3	0.5	0.4
UMC-FAB8A	0.9	1.3	1.4	1.4	5.0	4.8	4.2
UMC-FAB8B	9.5	12.0	10.8	7.8	40.1	38.2	118.5
TOTAL	11.1	13.9	12.6	9.5	47.1	60.4	123.1



WAFER FABRICATION GROUP

2001-2003 INDICES

Version 1.0 Initial Version
10/10/00

Fab 25:

- Copper process initiated in 1Q02
- Plated Bump processing initiated in 4Q02

Fab 30

- Plated Bump processing initiated in 4Q01

Version 2.0 Plan of Record for Budget/R12Q
12/04/00

Fab 14/15:

Capacity

- HV-7: Assumes sort equipment/hardware is compatible with HV-4. Trench Etch limited to a single machine.

Fab 25:

Capacity

- Removed projected support of HiP7L-SOI.
- Copper process initiated in 2Q02.
- Plated Bump schedule for 3Q02.

Defect Density Yspeed

- CS-50/H6 Yspeed modified to 0.85 in Yr2001 and 0.70 in Yr2002 – Yr2003.
- HiP7L-BULK Yspeed modified to 0.70 in Yr2002 – Yr2003

Sort Yield

- Modified NDW/Sort Yield

Wafer Transfer Price

- Added Wafer Transfer Prices for Plated Bump.

Capital Delivery

- Added Continuous Improvement, FMEA, and Technology.

Fab 30:

Capacity

- HiP7-BULK: Projected for 1Q02.
- HiP7-SOI: Projected for 3Q02.
- Bump Evap scheduled for 4Q01.
- Bump Plated scheduled for 3Q02.

Defect Density Yspeed

- All Yspeed changed to 0.70 except “Hammers”, which were changed to 0.85.

Sort Yield

- Changed “Tackhammer” HiP7-SOI die size from 76 mm² to 87 mm².
- Changed “Sledgehammer” HiP7-SOI die size from 250 mm² to 148 mm².

12/04/00

Fab8B**Sort Yield**

- Modified NDW/Sort Yield
- Separated Golem A/B.
- Added Anvil.

0.13u Foundry #1**Capacity**

- Modified to align to present required support.

Bump Capacity**Capacity**

- Modified to reflect no IBM support.
- Additional modifications to all support areas.

Wafer Transfer Price

- Added Fab 25 and Fab 30 Plated.

FASL

- Inputs for 1Q01 – 4Q01: Per FASL R6Q commitments
- Inputs for 1Q02 – 4Q03: Per FASL Business Plan JV4 200mm ver1.0

WFG Strategic Planning

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**FAB 25 3-YEAR PLAN
FAB CAPACITY (K - 8" WAFERS)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	2.5	2.5	2.5	2.5	10.0	2.5	2.5	2.5	2.5	10.0	1.5	1.5	1.5	1.5	6.0
CS-44E72(5LM)	1.0	1.0	1.0	1.0	4.0	1.0	1.0	1.0	1.0	4.0	1.0	1.0	1.0	1.0	4.0
CS-50/H6 (6LM)	59.0	59.0	59.0	59.0	236.0	59.0	54.4	44.4	36.6	194.4	30.9	30.9	27.1	24.0	112.9
EE7 (3LM)	0.5	0.0	0.0	0.0	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	2.0	12.0	20.0	34.0	27.0	27.0	30.0	35.0	119.0
TOTAL	63.0	62.5	62.5	62.5	250.5	62.5	59.9	59.9	60.1	242.4	60.4	60.4	59.6	61.5	241.9
Work Weeks	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0

**FAB 25 3-YEAR PLAN
DEFECT DENSITY (Do/Sq In)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	2.43	2.40	2.38	2.35	2.39	2.33	2.31	2.28	2.26	2.30	2.24	2.22	2.19	2.17	2.21
CS-44E72(5LM)	1.62	1.52	1.45	1.37	1.49	1.33	1.29	1.25	1.22	1.27	1.20	1.19	1.18	1.17	1.19
CS-50/H6 (6LM)	2.70	2.54	2.41	2.29	2.49	2.18	2.09	2.01	1.95	2.06	1.89	1.83	1.78	1.72	1.81
HiP7L-bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.00	2.70	2.43	2.19	2.44	1.97	1.85	1.74	1.63	1.80

**FAB 25 3-YEAR PLAN
DEFECT DENSITY (Yspeed)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00	1.00
CS-44E72(5LM)	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97	0.97
CS-50/H6 (6LM)	0.85	0.85	0.85	0.85	0.85	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70
HiP7L-bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70

**FAB 25 3-YEAR PLAN
DEFECT DENSITY (Y_{process})**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99
CS-44E72(5LM)	0.89	0.89	0.90	0.90	0.90	0.91	0.91	0.92	0.92	0.92	0.92	0.92	0.92	0.92	0.92
CS-50/H6 (6LM)	0.90	0.92	0.92	0.93	0.92	0.94	0.94	0.95	0.95	0.95	0.96	0.96	0.97	0.97	0.97
HiP7L-bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.79	0.82	0.84	0.82	0.87	0.89	0.90	0.91	0.89

**FAB 25 3-YEAR PLAN
DEFECT DENSITY (Y_{total})**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99	0.99
CS-44E72(5LM)	0.86	0.86	0.87	0.87	0.87	0.88	0.88	0.89	0.89	0.89	0.89	0.89	0.89	0.89	0.89
CS-50/H6 (6LM)	0.77	0.78	0.78	0.79	0.78	0.66	0.66	0.67	0.67	0.67	0.67	0.67	0.68	0.68	0.68
HiP7L-bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.55	0.57	0.59	0.57	0.61	0.62	0.63	0.64	0.63

**FAB 25 3-YEAR PLAN
CYCLE TIME--FAB (DAYS)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0	70.0
CS-44E72(5LM)	56.0	63.0	63.0	63.0	61.3	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0
CS-50/H6 (6LM)	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	70.0	70.0	66.5
EE7 (3LM)	98.0	0.0	0.0	0.0	98.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	70.0	63.0	63.0	65.3	63.0	63.0	63.0	63.0	63.0

Does not include either Wafer Bump or Wafer Sort Cycle Time.

**FAB 25 3-YEAR PLAN
PROCESS YIELD (%)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0	90.0
CS-44E72(5LM)	95.0	93.0	93.0	93.0	93.5	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0
CS-50/H6 (6LM)	94.0	95.0	95.0	95.0	94.8	95.0	95.0	95.0	95.0	95.0	95.0	95.0	93.0	93.0	94.0
EE7 (3LM)	90.0	0.0	0.0	0.0	90.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	85.0	90.0	91.0	88.7	92.0	93.0	94.0	95.0	93.5

**FAB 25 3-YEAR PLAN
SORT YIELD (NDW - 8" WAFERS)**

	Die Size Sq Mil	Die Size mm2	Gross Die	1Q01	2Q01	3Q01	4Q01	1Q02	2Q02	3Q02	4Q02	1Q03	2Q03	3Q03	4Q03
CMD/TMD															
CS-44E72 (5LM)															
K6-2	122	79	310	180	180	---	---	---	---	---	---	---	---	---	---
CS-50/H6 (6LM)															
K7-Duron -64K (Hot)	153	99	249	100	141	146	149	---	---	---	---	---	---	---	---
K7-Duron -64K (V Hot)	153	99	249	---	---	---	---	127	129	132	132	134	135	137	139
K7-Morgan -64K (Hot)	162	105	234	125	131	135	138	---	---	---	---	---	---	---	---
K7-Morgan -64K (V Hot)	162	105	234	---	---	---	---	118	120	122	122	124	126	128	129
K7-Thunderbird -256K (Hot)	183	118	195	75	105	109	111	---	---	---	---	---	---	---	---
K7-Thunderbird -256K (V)	183	118	195	---	---	---	---	96	97	99	99	101	102	104	105
HIP7L-bulk (7LM)															
K7-Morgan	109	70	363	---	---	---	---	---	159	170	179	187	193	199	203
EPD															
CS-34 (3LM)															
15040AR	103	66	398	300	300	300	300	300	300	300	300	300	300	300	300
29248CQ	65	42	638	550	550	550	550	550	550	550	550	550	550	550	550
48603AQ	65	42	602	520	520	520	520	520	520	520	520	520	520	520	520
CS-44E72 (5LM)															
K6-2	122	79	310	230	231	235	237	238	240	241	242	242	242	243	243
CS-50 (6LM)															
K6-2+	115	74	316	192	195	197	199	200	202	203	204	204	205	206	207
K7-Morgan	162	105	234	142	148	152	155	159	162	165	166	169	170	173	175
K7-Palomino	197	127	192	108	113	117	120	123	125	129	129	132	133	136	137

**FAB 25 3-YEAR PLAN
SORT YIELD (% - 8" WAFERS)**

	Die Size Sq Mil	Die Size mm2	Gross Die	1Q01	2Q01	3Q01	4Q01	1Q02	2Q02	3Q02	4Q02	1Q03	2Q03	3Q03	4Q03
CMD/TMD															
CS-44E72 (5LM)															
K6-2	122	79	310	58	58	---	---	---	---	---	---	---	---	---	---
CS-50/H6 (6LM)															
K7-Duron -64K (Hot)	153	99	249	40	57	59	60	---	---	---	---	---	---	---	---
K7-Duron -64K (V Hot)	153	99	249	---	---	---	---	51	52	53	53	54	54	55	56
K7-Morgan -64K (Hot)	162	105	234	53	56	58	59	---	---	---	---	---	---	---	---
K7-Morgan -64K (V Hot)	162	105	234	---	---	---	---	50	51	52	52	53	54	55	55
K7-Thunderbird -256K (Hot)	183	118	195	38	54	56	57	---	---	---	---	---	---	---	---
K7-Thunderbird -256K (V)	183	118	195	---	---	---	---	49	50	51	51	52	52	53	54
HIP7L-bulk (7LM)															
K7-Morgan	109	70	363	---	---	---	---	---	44	47	49	52	53	55	56
EPD															
CS-34 (3LM)															
15040AR	103	66	398	75	75	75	75	75	75	75	75	75	75	75	75
29248CQ	65	42	638	86	86	86	86	86	86	86	86	86	86	86	86
48603AQ	65	42	602	86	86	86	86	86	86	86	86	86	86	86	86
CS-44E72 (5LM)															
K6-2	122	79	310	74	75	76	76	77	77	78	78	78	78	78	78
CS-50 (6LM)															
K6-2+	115	74	316	61	62	62	63	63	64	64	65	65	65	65	66
K7-Morgan	162	105	234	61	63	65	66	68	69	71	71	72	73	74	75
K7-Palomino	197	127	192	56	59	61	63	64	65	67	67	69	69	71	71

**FAB 25 3-YEAR PLAN
THREE YEAR TRANSFER PRICES (8" Wafers)**

	2001	2002	2003
Bump Price - Evap	130	130	130
Bump Price - Plated	---	500	300
CS-34 (3LM)	1559	1559	1559
CS-44E72 (5LM)	1800	1728	1499
CS-50/H6 (6LM)	2146	2060	1788
EE7 (3LM)	1988	---	---
HiP7L-HD (7LM) Excl. Bump & PI	---	2460	2351
Polymide	25	25	25

**FAB 25 3-YEAR PLAN
CAPITAL DELIVERY (\$M)**

	2001	2002	2003
Continuous Improvement	31.7	32.0	32.0
Copper Conversion*	228.8	112.9	24.8
FMEA	3.7	2.0	2.0
Technology	11.3	---	---

* Includes facilities and C4 plating.

**FAB 30 3-YEAR PLAN
FAB CAPACITY (K - 8" WAFERS)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HIP6L (6LM)	26.0	32.6	38.4	36.8	133.8	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
HIP7L - bulk (7LM)	0.0	0.0	0.0	0.0	0.0	1.7	9.6	19.5	28.9	59.7	29.0	25.7	11.9	0.0	66.6
HIP7L - SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	64.9	190.1
TOTAL	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
Work Weeks	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0

**FAB 30 3-YEAR PLAN
DEFECT DENSITY (Do/Sq In)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.00	0.00	0.00	0.00	0.00	1.88	1.69	1.56	1.45	1.65	1.35	1.29	1.27	1.24	1.29
HIP6L (6LM)	1.96	1.77	1.59	1.43	1.69	1.29	1.16	1.09	1.04	1.15	1.02	1.00	1.00	1.00	1.01
HIP7L - bulk (7LM)	0.00	0.00	0.00	0.00	0.00	2.45	2.21	2.03	1.89	2.15	1.75	1.68	1.65	1.62	1.68
HIP7L - SOI (9LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.00	2.25	2.03	2.14	1.82	1.64	1.51	1.39	1.59

**FAB 30 3-YEAR PLAN
DEFECT DENSITY (Yspeed)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.00	0.00	0.00	0.00	0.00	0.85	0.85	0.85	0.85	0.85	0.85	0.85	0.85	0.85	0.85
HIP6L (6LM)	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70
HIP7L - bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70	0.70
HIP7L - SOI (9LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.85	0.85	0.85	0.85	0.85	0.85	0.85	0.85

**FAB 30 3-YEAR PLAN
DEFECT DENSITY (Yprocess)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.00	0.00	0.00	0.00	0.00	0.90	0.90	0.90	0.90	0.90	0.92	0.92	0.92	0.92	0.92
HIP6L (6LM)	0.88	0.89	0.90	0.90	0.89	0.90	0.91	0.91	0.91	0.91	0.92	0.92	0.92	0.92	0.92
HIP7L - bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.75	0.85	0.90	0.90	0.85	0.92	0.92	0.92	0.92	0.92
HIP7L - SOI (9LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.70	0.80	0.75	0.86	0.92	0.92	0.92	0.91

**FAB 30 3-YEAR PLAN
DEFECT DENSITY (Ytotal)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.00	0.00	0.00	0.00	0.00	0.77	0.77	0.77	0.77	0.77	0.78	0.78	0.78	0.78	0.78
HIP6L (6LM)	0.62	0.62	0.63	0.63	0.63	0.63	0.64	0.64	0.64	0.64	0.64	0.64	0.64	0.64	0.64
HIP7L - bulk (7LM)	0.00	0.00	0.00	0.00	0.00	0.53	0.60	0.63	0.63	0.60	0.64	0.64	0.64	0.64	0.64
HIP7L - SOI (9LM)	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.60	0.68	0.64	0.73	0.78	0.78	0.78	0.77

**FAB 30 3-YEAR PLAN
CYCLE TIME--FAB (DAYS)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.0	0.0	0.0	0.0	0.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0
HIP6L (6LM)	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0	63.0
HIP7L - bulk (7LM)	0.0	0.0	0.0	0.0	0.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0
HIP7L - SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0	84.0

Does not include either Wafer Bump or Wafer Sort Cycle Time.

**FAB 30 3-YEAR PLAN
PROCESS YIELD (%)**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HIP68 (9LM)	0.0	0.0	0.0	0.0	0.0	82.5	85.0	87.5	90.0	86.3	90.0	90.0	90.0	90.0	90.0
HIP6L (6LM)	91.0	92.0	93.0	93.0	92.3	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0	93.0
HIP7L - bulk (7LM)	0.0	0.0	0.0	0.0	0.0	85.0	87.5	90.0	90.0	88.1	90.0	90.0	90.0	90.0	90.0
HIP7L - SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	80.0	85.0	82.5	87.5	90.0	90.0	90.0	89.4

**FAB 30 3-YEAR PLAN
SORT YIELD (NDW - 8" WAFERS)**

	Die Size Sq Mil	Die Size mm2	Gross Die	1Q01	2Q01	3Q01	4Q01	1Q02	2Q02	3Q02	4Q02	1Q03	2Q03	3Q03	4Q03
CMD/TMD															
HIP68 (9LM)															
K8-Clawhammer -256K	245	158	152	---	---	---	---	79	83	85	88	91	93	93	94
K8-Sledgehammer	388	250	92	---	---	---	---	40	42	44	46	49	50	50	50
HIP6L (6LM)															
K7-7309A Tb6 -256K	187	121	204	118	99	104	106	107	111	112	113	115	115	115	115
K7-Morgan -64K	164	106	234	---	113	117	120	123	127	129	130	131	132	132	132
K7-Palomino -256K	200	129	192	51	88	92	95	97	101	102	103	105	105	105	105
HIP7L (7LM)															
K7-Morgan -64K	109	70	363	---	---	---	---	152	176	190	192	199	201	202	202
K7-Palomino -256K	136	88	285	---	---	---	---	113	132	142	145	151	152	153	153
HIP7L (9LM)															
K8-Clawhammer -256K	146	94	266	---	---	---	---	---	---	124	145	157	172	175	178
K8-Sledgehammer	229	148	163	---	---	---	---	---	---	68	80	87	96	98	101
K8-Tackhammer -128K	135	87	289	---	---	---	---	---	---	137	159	173	189	192	195

**FAB 30 3-YEAR PLAN
SORT YIELD (% - 8" WAFERS)**

	Die Size Sq Mil	Die Size mm2	Gross Die	1Q01	2Q01	3Q01	4Q01	1Q02	2Q02	3Q02	4Q02	1Q03	2Q03	3Q03	4Q03
CMD/TMD															
HIP68 (9LM)															
K8-Clawhammer -256K	245	158	152	---	---	---	---	52	55	56	58	60	61	61	62
K8-Sledgehammer	388	250	92	---	---	---	---	43	46	48	50	53	54	54	54
HIP6L (6LM)															
K7-7309A Tb6 -256K	187	121	204	58	49	51	52	52	54	55	55	56	56	56	56
K7-Morgan -64K	164	106	234	---	48	50	51	53	54	55	56	56	56	56	56
K7-Palomino -256K	200	129	192	27	46	48	49	51	53	53	54	55	55	55	55
HIP7L (7LM)															
K7-Morgan -64K	109	70	363	---	---	---	---	42	48	52	53	55	55	56	56
K7-Palomino -256K	136	88	285	---	---	---	---	40	46	50	51	53	53	54	54
HIP7L (9LM)															
K8-Clawhammer -256K	146	94	266	---	---	---	---	---	---	47	55	59	65	66	67
K8-Sledgehammer	229	148	163	---	---	---	---	---	---	42	49	53	59	60	62
K8-Tackhammer -128K	135	87	289	---	---	---	---	---	---	47	55	60	65	66	67

**FAB 30 3-YEAR PLAN
THREE YEAR TRANSFER PRICES (8" Wafers)**

	2001	2002	2003
HiP68 (9LM) Excl. Bump & PI	---	3974	2625
HiP6L (6LM) Excl. Bump & PI	2555	2006	1875
HiP7L - bulk (7LM) Excl. Bump & PI	---	2628	2195
HiP7L - SOI (9LM) Excl. Bump & PI	---	3300	2509

**FAB 30 3-YEAR PLAN
CAPITAL DELIVERY (\$M)**

	2001	2002	2003
Equipment - C4	31.0	10.2	16.4
Equipment - FAB	347.4	175.0	83.1
Facilities	73.0	16.0	6.6
Other	12.4	9.1	8.3



WAFER FABRICATION GROUP

2001-2003 WAFER OUT DEMAND/COMMITTS

Version 1.0 Based on CPG Plan 044C, not published

Version 2.0 Plan of Record for Budget/R12Q
12/04/00

Fab 14/15:

- HV4: Demands exceed Commits in 1Q01 – 3Q01
- HV-7: Assumes sort equipment/hardware is compatible with HV-4. Trench Etch is limited to a single machine.

Fab25:

- Demands and Commits are aligned for all periods.
- Copper process initiated in 2Q02
- CPG demands based on Plan 047A

Fab30:

- Demands exceed Commits in 3Q01, 4Q01, and 4Q03
- HiP7-BULK: Projected for 1Q02
- HiP7-SOI: Projected for 3Q02
- CPG demands based on Plan 047A
- All capacity fully utilized.

Fab8A:

- Demands and Commits are aligned for all periods.

Fab8B:

- Demands and Commits are aligned for all periods.
- Commits exceed Capacity in Yr2003. Foundry Services will work with UMC to insure support.

Sony:

- Demands and Commits are aligned for all periods.

Epson:

- Demands and Commits are aligned for all periods.

TSMC:

- Demands and Commits are aligned for all periods.

0.13u Foundry #1:

- Based on CPG Plan 047A
- Demands and Commits are aligned for all periods.

FASL:

- **Capacity**
1Q01 - 4Q01: Per FASL R6Q commitments.
1Q02 - 4Q03: Per FASL Business Plan JV4 200mm ver 1.0
All Capacity fully utilized.
- **Demands**
Demands Source – Business Plan JV4 200mm ver 1.0
Demands exceed Commits in 1Q01 to 4Q03 on numerous technologies.
- **New Technologies introduced as follows:**
CS-99SB: Projected for 2Q01.
CS-59S: Projected for 4Q01.
CS-49NSD: Projected for 1Q02.
CS-99DB: Projected for 2Q02.
CS-59N: Projected for 3Q02.
CS-109DBH: Projected for 4Q02.



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**TREE-YEAR PLAN
FAB 14/15 WAFER OUT DEMANDS (K, 6")**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
EPD TOTAL	7.5	9.3	8.8	7.6	33.1	7.0	6.5	6.0	5.1	24.6	4.9	5.0	4.7	4.3	19.0
CS-21	0.2	0.1	0.2	0.1	0.6	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
CS-21S	3.3	4.3	4.1	3.1	14.8	2.6	2.6	2.5	2.1	9.8	1.8	1.9	1.8	1.6	7.1
CS-22	0.4	0.5	0.5	0.4	1.8	0.2	0.2	0.2	0.1	0.7	0.0	0.0	0.0	0.0	0.0
CS-23	3.7	4.3	4.0	4.0	16.0	4.2	3.7	3.3	2.9	14.2	3.2	3.1	2.9	2.7	11.8
LATTICE TOTAL	12.0	12.0	12.0	12.0	48.0	12.0	12.0	12.0	12.0	48.0	12.0	12.0	12.0	12.0	48.0
EE4	1.7	1.5	1.0	1.0	5.2	0.8	0.8	0.8	0.8	3.0	0.8	0.8	0.8	0.8	3.0
EE5	6.5	6.0	6.0	5.5	24.0	3.8	3.8	3.8	3.8	15.0	3.8	3.8	3.8	3.8	15.0
EE65	3.9	4.5	5.0	5.5	18.9	7.5	7.5	7.5	7.5	30.0	7.5	7.5	7.5	7.5	30.0
LEGERITY TOTAL	35.3	38.7	41.2	36.6	151.9	37.5	41.7	44.3	45.3	168.7	46.2	47.8	49.7	51.2	194.8
CS-21	5.2	4.7	3.9	2.8	16.6	2.6	2.4	2.5	2.5	10.0	2.4	2.4	2.4	2.4	9.7
CS-21ST	2.0	2.2	2.0	1.8	8.1	2.1	1.9	1.8	1.8	7.5	1.8	1.8	1.8	1.7	7.1
CS-23	13.0	13.1	12.6	11.2	50.0	13.3	12.5	12.5	12.6	50.9	12.1	12.2	12.3	12.0	48.5
HV4	13.5	15.6	17.1	14.6	60.7	10.5	10.7	10.0	9.8	40.9	9.8	10.0	10.1	10.2	40.0
HV4+	1.3	0.9	1.1	1.3	4.5	4.0	8.9	11.8	12.6	37.3	13.6	14.6	15.7	16.9	60.7
HV7	0.3	2.2	4.5	4.9	12.0	5.0	5.3	5.7	6.0	22.0	6.5	6.9	7.5	8.0	28.8
NPD TOTAL	13.1	12.9	12.4	12.1	50.5	9.6	9.5	8.9	8.9	36.8	7.8	7.8	7.3	7.3	30.1
CS-21	0.2	0.2	0.2	0.2	0.8	0.2	0.2	0.2	0.2	0.6	0.2	0.2	0.1	0.1	0.6
CS-21S	12.9	12.7	12.2	11.9	49.7	9.4	9.4	8.7	8.7	36.2	7.6	7.6	7.2	7.2	29.5
NVD TOTAL	7.0	5.3	7.0	6.8	26.1	5.0	5.1	5.3	5.1	20.5	5.0	5.0	5.0	5.0	20.0
CS-19A/AR	0.5	0.7	0.9	0.7	2.8	0.7	0.0	0.0	0.0	0.7	0.8	0.8	0.8	0.8	3.2
CS-19B	1.6	1.6	1.8	2.1	7.2	2.2	3.0	2.9	3.0	11.0	4.2	4.2	4.2	4.2	16.8
CS-19BF	0.9	0.0	0.0	0.0	0.9	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	
CS-19BR	4.0	3.0	4.3	4.0	15.3	2.2	2.2	2.3	2.1	8.8	0.0	0.0	0.0	0.0	0.0
TOTAL FAB	74.9	78.1	81.4	75.2	309.6	71.1	74.9	76.4	76.3	298.7	75.9	77.6	78.7	79.8	311.9

**THREE-YEAR PLAN
Fab 25 WAFER OUT DEMANDS (K, 8")**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
CMD/TMD TOTAL	59.9	55.5	58.4	57.8	231.6	57.1	54.3	53.8	48.5	213.7	26.8	23.1	27.1	30.9	107.9
CS-44E72 (5LM)	5.3	0.0	0.0	0.0	5.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
CS-50/H6 (6LM)	54.6	55.5	58.4	57.8	226.3	57.1	51.9	41.8	28.5	179.3	2.6	0.0	0.0	0.0	2.6
HP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	2.4	12.0	20.0	34.4	24.2	23.1	27.1	30.9	105.3
EPD TOTAL	1.8	2.9	3.7	3.9	12.3	3.9	4.4	4.7	4.5	17.5	3.9	3.8	3.8	3.6	15.1
CS-34 (3LM)	1.5	1.6	2.1	2.0	7.2	1.5	1.6	1.6	1.5	6.2	1.1	1.2	1.2	1.1	4.6
CS-44E72 (5LM)	0.1	0.7	0.6	0.6	2.0	0.5	0.5	0.5	0.4	1.9	0.3	0.3	0.3	0.3	1.2
CS-50/H6 (6LM)	0.2	0.6	1.0	1.3	3.1	1.9	2.3	2.6	2.6	9.4	2.5	2.3	2.3	2.2	9.3
Lattice TOTAL	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
EE7 (3LM)	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TOTAL FAB	61.8	58.4	62.1	61.7	244.0	61.0	58.7	58.5	53.0	231.2	30.7	26.9	30.9	34.5	123.0

**THREE-YEAR PLAN
Fab 30 WAFER OUT DEMANDS (K, 8")**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
CMD/TMD TOTAL	26.0	32.6	41.2	47.6	147.4	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	69.0	260.8
HIP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HIP6L (6LM)	26.0	32.6	41.2	47.6	147.4	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
HIP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	1.7	9.6	19.5	28.9	59.7	29.0	25.7	11.9	0.0	66.6
HIP7L-SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	69.0	194.2
TOTAL FAB	26.0	32.6	41.2	47.6	147.4	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	69.0	260.8

**THREE-YEAR PLAN
FASL 1 SORT OUT DEMANDS (K, 8")
AMD ONLY**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
NVD TOTAL	45.0	44.9	47.3	48.6	185.8	51.0	48.9	50.9	52.1	202.9	45.7	46.0	49.2	49.4	190.3
CS-39S	45.0	44.9	47.3	48.6	185.8	51.0	48.9	50.9	52.1	202.9	45.7	43.5	43.5	40.3	173.0
CS-99DB	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	2.5	5.7	9.1	17.3
TOTAL FAB	45.0	44.9	47.3	48.6	185.8	51.0	48.9	50.9	52.1	202.9	45.7	46.0	49.2	49.4	190.3

**THREE-YEAR PLAN
FASL 2 SORT OUT DEMANDS (K, 8")
AMD ONLY**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
NVD TOTAL	45.5	58.9	71.9	79.6	255.9	85.5	91.2	60.7	46.2	283.6	49.7	47.7	46.2	45.8	189.4
CS-109DBH	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	2.2	11.9	17.5	21.4	53.0
CS-49N/NS	11.7	14.9	16.7	20.3	63.6	23.3	22.9	5.9	6.0	58.1	6.8	6.5	0.0	0.0	13.3
CS-49NSD	0.0	0.0	2.8	4.5	7.3	4.9	6.9	0.6	0.6	13.0	0.0	0.0	0.0	0.0	0.0
CS-49S/HS	33.8	43.8	42.3	44.6	164.5	44.8	27.2	25.5	18.3	115.8	14.0	3.8	0.0	0.0	17.8
CS-99DB	0.0	0.0	0.0	0.0	0.0	0.0	32.9	27.3	19.9	80.1	25.3	25.5	28.7	24.4	103.9
CS-99SB	0.0	0.2	10.1	10.2	20.5	12.5	1.3	1.4	1.4	16.6	1.4	0.0	0.0	0.0	1.4
TOTAL FAB	45.5	58.9	71.9	79.6	255.9	85.5	91.2	60.7	46.2	283.6	49.7	47.7	46.2	45.8	189.4

**THREE-YEAR PLAN
FASL 3 SORT OUT DEMANDS (K, 8")
AMD ONLY**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
NVD TOTAL	0.0	0.0	0.0	10.8	10.8	10.8	22.7	55.1	95.3	183.9	93.8	104.1	100.8	114.1	412.8
CS-109DBH	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	13.1	13.1	7.1	14.5	11.2	15.8	48.6
CS-59N	0.0	0.0	0.0	0.0	0.0	0.0	9.1	28.9	50.6	88.6	54.7	68.3	69.7	83.4	276.1
CS-59S	0.0	0.0	0.0	10.8	10.8	10.8	13.6	26.2	31.6	82.2	32.0	21.3	19.9	14.9	88.1
TOTAL FAB	0.0	0.0	0.0	10.8	10.8	10.8	22.7	55.1	95.3	183.9	93.8	104.1	100.8	114.1	412.8

**THREE-YEAR PLAN
FASL 4 SORT OUT DEMANDS (K, 8")
AMD ONLY**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
NVD TOTAL	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	4.2	4.2	7.9	20.2	30.8	41.6	100.5
CS-109DBH	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	4.2	4.2	7.9	20.2	30.8	41.6	100.5
TOTAL FAB	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	4.2	4.2	7.9	20.2	30.8	41.6	100.5

**THREE-YEAR PLAN
Fab 25 WAFER OUT COMMITS (K, 8")**

PRODUCT LINE	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CMD/TMD TOTAL	59.9	55.5	58.4	57.8	231.6	57.1	54.3	53.8	48.5	213.7	26.8	23.1	27.1	30.9	107.9
CS-44E72 (5LM)	5.3	0.0	0.0	0.0	5.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
CS-50/H6 (6LM)	54.6	55.5	58.4	57.8	226.3	57.1	51.9	41.8	28.5	179.3	2.6	0.0	0.0	0.0	2.6
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	2.4	12.0	20.0	34.4	24.2	23.1	27.1	30.9	105.3
EPD TOTAL	1.8	2.9	3.7	3.9	12.3	3.9	4.4	4.7	4.5	17.5	3.9	3.8	3.8	3.6	15.1
CS-34 (3LM)	1.5	1.6	2.1	2.0	7.2	1.5	1.6	1.6	1.5	6.2	1.1	1.2	1.2	1.1	4.6
CS-44E72 (5LM)	0.1	0.7	0.6	0.6	2.0	0.5	0.5	0.5	0.4	1.9	0.3	0.3	0.3	0.3	1.2
CS-50/H6 (6LM)	0.2	0.6	1.0	1.3	3.1	1.9	2.3	2.6	2.6	9.4	2.5	2.3	2.3	2.2	9.3
Lattice TOTAL	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
EE7 (3LM)	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TOTAL FAB	61.8	58.4	62.1	61.7	244.0	61.0	58.7	58.5	53.0	231.2	30.7	26.9	30.9	34.5	123.0

**THREE-YEAR PLAN
Fab 25 WAFER OUT COMMITS (K, 8")**

TECHNOLOGY	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	1.5	1.6	2.1	2.0	7.2	1.5	1.6	1.6	1.5	6.2	1.1	1.2	1.2	1.1	4.6
CS-44E72 (5LM)	5.4	0.7	0.6	0.6	7.3	0.5	0.5	0.5	0.4	1.9	0.3	0.3	0.3	0.3	1.2
CS-50/H6 (6LM)	54.8	56.1	59.4	59.1	229.4	59.0	54.2	44.4	31.1	188.7	5.1	2.3	2.3	2.2	11.9
EE7 (3LM)	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	2.4	12.0	20.0	34.4	24.2	23.1	27.1	30.9	105.3
TOTAL FAB	61.8	58.4	62.1	61.7	244.0	61.0	58.7	58.5	53.0	231.2	30.7	26.9	30.9	34.5	123.0

**THREE-YEAR PLAN
FAB 25 WAFER OUT CAPACITY (K, 8")**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CS-34 (3LM)	2.5	2.5	2.5	2.5	10.0	2.5	2.5	2.5	2.5	10.0	1.5	1.5	1.5	1.5	6.0
CS-44E72(5LM)	1.0	1.0	1.0	1.0	4.0	1.0	1.0	1.0	1.0	4.0	1.0	1.0	1.0	1.0	4.0
CS-50/H6 (6LM)	59.0	59.0	59.0	59.0	236.0	59.0	54.4	44.4	36.6	194.4	30.9	30.9	27.1	24.0	112.9
EE7 (3LM)	0.5	0.0	0.0	0.0	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	0.0	2.0	12.0	20.0	34.0	27.0	27.0	30.0	35.0	119.0
TOTAL	63.0	62.5	62.5	62.5	250.5	62.5	59.9	59.9	60.1	242.4	60.4	60.4	59.6	61.5	241.9
Work Weeks	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0

**THREE-YEAR PLAN
Fab 30 WAFER OUT COMMITS (K, 8")**

PRODUCT LINE	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
CMD/TMD TOTAL	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
HiP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HiP6L (6LM)	26.0	32.6	38.4	36.8	133.8	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	1.7	9.6	19.5	28.9	59.7	29.0	25.7	11.9	0.0	66.6
HiP7L-SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	64.9	190.1
TOTAL FAB	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7

**THREE-YEAR PLAN
Fab 30 WAFER OUT COMMITS (K, 8")**

TECHNOLOGY	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HiP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HiP6L (6LM)	26.0	32.6	38.4	36.8	133.8	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	1.7	9.6	19.5	28.9	59.7	29.0	25.7	11.9	0.0	66.6
HiP7L-SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	64.9	190.1
TOTAL FAB	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7

**THREE-YEAR PLAN
FAB 30 WAFER OUT CAPACITY (K, 8")**

	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
HiP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HiP6L (6LM)	26.0	32.6	38.4	36.8	133.8	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
7L - bulk	0.0	0.0	0.0	0.0	0.0	1.7	9.6	19.5	28.9	59.7	29.0	25.7	11.9	0.0	66.6
HiP7L - SOI	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	64.9	190.1
TOTAL	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
Work Weeks	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0	13.0	13.0	13.0	13.0	52.0

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS VS. CAPACITIES (K, 8")
 BY FAB**

	<u>1Q02</u>			<u>2Q02</u>			<u>3Q02</u>			<u>4Q02</u>			<u>2002</u>		
	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>
0.13u Fdry #1 - (BULK)	6.0	6.0	0.0	3.8	3.8	0.0	5.9	5.9	0.0	1.1	1.1	0.0	16.9	16.9	0.0
EPSON	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 14/15	39.9	46.2	6.3	42.1	46.2	4.2	42.9	46.2	3.3	42.9	46.2	3.4	167.8	184.9	17.1
Fab 25	61.0	62.5	1.5	58.7	59.9	1.2	58.5	59.9	1.4	53.0	60.1	7.1	231.2	242.4	11.2
Fab 30	46.0	46.0	0.0	52.8	52.8	0.0	54.7	54.7	0.0	58.9	58.9	0.0	212.5	212.5	0.0
Fab8A	1.2	2.0	0.8	1.2	2.0	0.8	1.2	2.0	0.8	1.2	2.0	0.8	4.8	8.0	3.2
Fab8B	8.4	19.1	10.7	7.7	19.1	11.4	9.1	19.1	10.0	13.0	19.1	6.1	38.2	76.4	38.2
FASL - GMD	27.0	27.0	0.0	25.8	25.8	0.0	27.8	27.8	0.0	36.0	36.0	0.0	116.6	116.6	0.0
FASL - IWATE	15.1	15.1	0.0	14.5	14.5	0.0	13.4	13.4	0.0	14.0	14.0	0.0	57.0	57.0	0.0
FASL 1	48.0	48.0	0.0	45.6	45.6	0.0	45.6	45.6	0.0	45.6	45.6	0.0	184.8	184.8	0.0
FASL 2	35.7	35.7	0.0	36.9	36.9	0.0	37.7	37.7	0.0	40.4	40.4	0.0	150.6	150.6	0.0
FASL 3	0.0	0.0	0.0	12.9	12.9	0.0	26.3	26.3	0.0	36.2	36.2	0.0	75.4	75.4	0.0
FASL 4	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.5	0.5	0.0	0.5	0.5	0.0
SONY	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TSMC	0.1	0.2	0.1	0.1	0.2	0.1	0.1	0.2	0.1	0.1	0.2	0.1	0.5	0.8	0.3
TOTAL FAB	288.4	307.8	19.3	302.2	319.8	17.6	323.3	338.9	15.6	342.9	360.3	17.4	1256.8	1326.8	70.0

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS VS. CAPACITIES (K, 8")
 BY FAB**

	<u>1Q03</u>			<u>2Q03</u>			<u>3Q03</u>			<u>4Q03</u>			<u>2003</u>		
	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>	<u>COM</u>	<u>CAP</u>	<u>DEL</u>
0.13u Fdry #1 - (BULK)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
EPSON	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 15	42.6	46.2	3.6	43.6	46.2	2.6	44.2	46.2	2.0	44.8	46.2	1.4	175.2	184.9	9.7
Fab 25	30.7	60.4	29.7	26.9	60.4	33.5	30.9	59.6	28.7	34.5	61.5	27.0	123.0	241.9	118.9
Fab 30	62.9	62.9	0.0	63.9	63.9	0.0	65.0	65.0	0.0	64.9	64.9	0.0	256.7	256.7	0.0
Fab8A	1.1	2.0	0.9	1.1	2.0	0.9	1.0	2.0	1.0	1.0	2.0	1.0	4.2	8.0	3.8
Fab8B	19.5	19.1	-0.4	25.9	19.1	-6.8	31.8	19.1	-12.7	41.4	19.1	-22.3	118.5	76.4	-42.1
FASL - GMD	38.5	38.5	0.0	41.2	41.2	0.0	44.1	44.1	0.0	46.7	46.7	0.0	170.5	170.5	0.0
FASL - IWATE	17.1	17.1	0.0	17.9	17.9	0.0	18.9	18.9	0.0	18.9	18.9	0.0	72.6	72.6	0.0
FASL 1	39.0	39.0	0.0	41.2	41.2	0.0	44.8	44.8	0.0	44.9	44.9	0.0	169.8	169.8	0.0
FASL 2	43.0	43.0	0.0	42.3	42.3	0.0	42.1	42.1	0.0	41.6	41.6	0.0	168.9	168.9	0.0
FASL 3	46.2	46.2	0.0	48.5	48.5	0.0	51.9	51.9	0.0	52.3	52.3	0.0	198.8	198.8	0.0
FASL 4	5.5	5.5	0.0	16.0	16.0	0.0	28.0	28.0	0.0	37.8	37.8	0.0	87.3	87.3	0.0
SONY	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TSMC	0.1	0.2	0.1	0.1	0.2	0.1	0.1	0.2	0.1	0.1	0.2	0.1	0.4	0.8	0.4
TOTAL FAB	346.1	380.0	34.0	368.4	398.8	30.4	402.6	421.7	19.1	428.8	436.0	7.2	1545.8	1636.5	90.7

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS (K, 8")
 BY FAB**

FAB/FOUNDRY	1Q01	2Q01	3Q01	4Q01	2001	1Q02	2Q02	3Q02	4Q02	2002	1Q03	2Q03	3Q03	4Q03	2003
0.13u Fdry #1 - (BULK)	0.0	0.0	0.0	0.0	0.0	6.0	3.8	5.9	1.1	16.9	0.0	0.0	0.0	0.0	0.0
EPSON	0.1	0.1	0.1	0.1	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 14/15	41.6	41.8	43.1	42.3	168.7	39.9	42.1	42.9	42.9	167.8	42.6	43.6	44.2	44.8	175.2
Fab 25	61.8	58.4	62.1	61.7	244.0	61.0	58.7	58.5	53.0	231.2	30.7	26.9	30.9	34.5	123.0
Fab 30	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
Fab8A	0.9	1.3	1.4	1.4	5.0	1.2	1.2	1.2	1.2	4.8	1.1	1.1	1.0	1.0	4.2
Fab8B	9.7	11.9	10.7	7.7	40.0	8.4	7.7	9.1	13.0	38.2	19.5	25.9	31.8	41.4	118.5
FASL - GMD	8.7	10.7	14.3	24.2	57.9	27.0	25.8	27.8	36.0	116.6	38.5	41.2	44.1	46.7	170.5
FASL - IWATE	17.0	16.3	16.6	17.6	67.5	15.1	14.5	13.4	14.0	57.0	17.1	17.9	18.9	18.9	72.6
FASL 1	45.0	44.7	47.3	48.0	185.0	48.0	45.6	45.6	45.6	184.8	39.0	41.2	44.8	44.9	169.8
FASL 2	27.9	31.1	33.6	35.6	128.1	35.7	36.9	37.7	40.4	150.6	43.0	42.3	42.1	41.6	168.9
FASL 3	0.0	0.0	0.0	0.5	0.5	0.0	12.9	26.3	36.2	75.4	46.2	48.5	51.9	52.3	198.8
FASL 4	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.5	0.5	5.5	16.0	28.0	37.8	87.3
SONY	0.6	0.4	0.2	0.1	1.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TSMC	0.0	0.1	0.1	0.1	0.3	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.4
TOTAL FAB	239.2	249.5	267.8	276.1	1032.	288.4	302.2	323.3	342.9	1256.	346.1	368.4	402.6	428.8	1545.8

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS (K, 8")
 BY GEOMETRY**

MICRON SIZE	1001	2001	3001	4001	2001	1002	2002	3002	4002	2002	1003	2003	3003	4003	2003
>0.25u TOTAL	0.0	0.1	0.1	0.1	0.3	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.4
0.35u 2P3M	0.0	0.1	0.1	0.1	0.3	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.4
>0.5u TOTAL	42.5	42.7	43.8	43.0	171.9	40.4	42.5	43.4	43.3	169.5	43.1	44.0	44.6	45.2	176.9
0.32u 1P3M	0.2	0.3	0.4	0.5	1.4	0.4	0.4	0.4	0.4	1.7	0.4	0.4	0.4	0.4	1.7
CS-19A/AR	0.3	0.4	0.5	0.4	1.6	0.4	0.0	0.0	0.0	0.4	0.5	0.5	0.4	0.4	1.8
CS-19B	0.9	0.9	1.0	1.2	4.0	1.2	1.7	1.7	1.7	6.2	2.3	2.3	2.4	2.4	9.4
CS-19BF	0.5	0.0	0.0	0.0	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
CS-19BR	2.3	1.7	2.4	2.3	8.6	1.2	1.2	1.3	1.2	4.9	0.0	0.0	0.0	0.0	0.0
CS-21	3.1	2.9	2.4	1.7	10.1	1.6	1.5	1.5	1.5	6.0	1.4	1.4	1.4	1.4	5.8
CS-21S	9.1	9.5	9.1	8.4	36.2	6.8	6.7	6.3	6.1	25.8	5.3	5.4	5.0	4.9	20.6
CS-21ST	1.2	1.3	1.1	1.0	4.6	1.2	1.0	1.0	1.0	4.2	1.0	1.0	1.0	1.0	4.0
CS-22	0.2	0.3	0.3	0.2	1.0	0.1	0.1	0.1	0.0	0.4	0.0	0.0	0.0	0.0	0.0
CS-23	9.4	9.8	9.4	8.6	37.1	9.9	9.1	8.9	8.7	36.6	8.6	8.6	8.5	8.2	33.9
EE4	0.9	0.8	0.6	0.6	2.9	0.4	0.4	0.4	0.4	1.7	0.4	0.4	0.4	0.4	1.7
EE5	3.7	3.4	3.4	3.1	13.5	2.1	2.1	2.1	2.1	8.4	2.1	2.1	2.1	2.1	8.4
EE65	2.2	2.5	2.8	3.1	10.6	4.2	4.2	4.2	4.2	16.9	4.2	4.2	4.2	4.2	16.9
HV4	7.2	6.7	6.9	8.2	28.9	5.9	6.0	5.6	5.5	23.0	5.5	5.6	5.7	5.7	22.5
HV4+	0.7	0.5	0.6	0.7	2.6	2.2	5.0	6.6	7.1	21.0	7.6	8.2	8.8	9.5	34.1
HV7	0.2	1.3	2.5	2.8	6.7	2.8	3.0	3.2	3.4	12.4	3.6	3.9	4.2	4.5	16.2
IMOX2	0.3	0.2	0.0	0.0	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
IMOX2S	0.2	0.1	0.0	0.0	0.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
LS	0.0	0.1	0.2	0.1	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
SMS12-6"	0.0	0.0	0.0	0.0	0.2	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
SMSDL-5"	0.1	0.1	0.1	0.1	0.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
0.13 TOTAL	0.0	0.0	0.0	0.0	0.0	6.0	3.8	5.9	1.1	16.9	0.0	0.0	0.0	0.0	0.0
0.13u Technology	0.0	0.0	0.0	0.0	0.0	6.0	3.8	5.9	1.1	16.9	0.0	0.0	0.0	0.0	0.0
0.13u TOTAL	0.0	0.0	0.0	0.0	0.0	1.7	12.0	41.9	72.2	127.8	87.1	87.0	92.1	95.8	362.0
HiP7L-bulk (7LM)	0.0	0.0	0.0	0.0	0.0	1.7	12.0	31.5	48.9	94.1	53.2	48.8	39.0	30.9	171.9
HiP7L-SOI (9LM)	0.0	0.0	0.0	0.0	0.0	0.0	0.0	10.4	23.3	33.7	34.0	38.1	53.1	64.9	190.1
0.18u TOTAL	80.8	88.7	97.8	96.6	363.9	104.2	112.0	99.0	81.0	396.2	70.5	94.3	120.4	141.4	426.6
0.18u 1P5M	0.0	0.0	0.0	0.2	0.2	0.8	1.5	2.0	2.2	6.4	1.8	1.3	0.8	0.9	4.8
0.18u 1P6M	0.0	0.0	0.0	0.0	0.0	0.0	0.0	1.2	3.9	5.2	9.3	15.1	20.1	27.4	71.8
0.18u 5LM	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.1	0.1	0.4	0.2	0.2	0.2	0.2	0.9
0.18u 6LM	0.0	0.0	0.0	0.0	0.0	0.1	0.1	0.2	0.2	0.6	0.7	0.7	1.2	1.2	3.8
CS-109DBH	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	2.3	2.3	13.3	42.5	59.5	78.8	194.1
CS-50/H6 (6LM)	54.8	56.1	59.4	59.1	229.4	59.0	54.2	44.4	31.1	188.7	5.1	2.3	2.3	2.2	11.9
CS-59N	0.0	0.0	0.0	0.0	0.0	0.0	0.0	1.4	3.3	4.7	8.1	10.9	16.4	15.8	51.2
CS-59S	0.0	0.0	0.0	0.5	0.5	0.0	12.9	24.9	31.2	69.0	32.0	21.3	19.9	14.9	88.1
HiP68 (9LM)	0.0	0.0	0.0	0.0	0.0	3.4	6.0	2.3	0.0	11.8	0.0	0.0	0.0	0.0	0.0
HiP6L (6LM)	26.0	32.6	38.4	36.8	133.8	40.9	37.3	22.5	6.7	107.4	0.0	0.0	0.0	0.0	0.0
0.22u TOTAL	52.8	57.3	63.1	75.1	248.3	72.7	68.0	63.5	58.3	262.5	42.8	23.9	8.5	0.0	75.2
CS-49S/HS	52.8	57.3	63.1	75.1	248.3	72.7	68.0	63.5	58.3	262.5	42.8	23.9	8.5	0.0	75.2
0.23u TOTAL	0.0	0.2	0.8	1.9	2.8	3.5	7.7	13.9	30.6	55.7	51.0	66.3	85.7	96.0	299.0
CS-99DB	0.0	0.0	0.0	0.0	0.0	0.0	6.4	12.6	29.2	48.1	49.6	66.3	85.7	96.0	297.6
CS-99SB	0.0	0.2	0.8	1.9	2.8	3.5	1.3	1.4	1.4	7.5	1.3	0.0	0.0	0.0	1.3
0.25u TOTAL	15.7	12.7	11.5	8.3	48.2	9.3	7.9	7.3	8.2	32.8	10.7	11.7	9.6	11.8	43.8
0.25u 1P4M	9.6	10.1	8.7	5.9	34.3	7.1	5.9	5.4	6.3	24.7	7.3	8.3	9.2	11.3	36.1
0.25u 1P5M	0.0	1.2	1.6	1.4	4.2	0.4	0.1	0.1	0.1	0.7	0.1	0.1	0.1	0.2	0.5
CS-44E72 (5LM)	5.4	0.7	0.6	0.6	7.3	0.5	0.5	0.5	0.4	1.9	0.3	0.3	0.3	0.3	1.2
CS-49N/NS	0.7	0.7	0.6	0.4	2.3	1.3	1.4	1.4	1.4	5.4	3.0	3.0	0.0	0.0	6.0
0.35u TOTAL	47.4	47.8	50.8	51.1	197.1	50.5	48.2	48.2	48.1	195.0	40.9	41.0	41.6	38.5	162.0
0.35u 1P3M	0.8	1.5	1.4	1.1	4.8	0.8	0.8	0.8	0.9	3.4	0.8	0.8	0.8	0.8	3.2
CS-34 (3LM)	1.5	1.6	2.1	2.0	7.2	1.5	1.6	1.6	1.5	6.2	1.1	1.2	1.2	1.1	4.6
CS-39S	45.0	44.7	47.3	48.0	185.0	48.0	45.6	45.6	45.6	184.8	39.0	39.0	39.6	36.6	154.2
CS-49NSD	0.0	0.0	0.0	0.0	0.0	0.2	0.1	0.1	0.1	0.6	0.0	0.0	0.0	0.0	0.0
EE7 (3LM)	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
TOTAL FAB	239.2	249.5	267.8	276.1	1032.6	288.4	302.2	323.3	342.9	1256.8	346.1	368.4	402.6	428.8	1545.8

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS (K, 8")
 BY GROUP BY FAB**

	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
CPG	110.5	117.3	124.9	119.1	471.8	132.1	133.4	137.9	135.2	538.7	121.4	125.0	135.5	148.5	530.3
TSMC	0.0	0.1	0.1	0.1	0.3	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.4
EPSON	0.1	0.1	0.1	0.1	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 14/15	11.6	12.4	11.9	11.1	47.0	9.3	9.0	8.3	7.9	34.5	7.1	7.2	6.7	6.5	27.6
Fab 25	61.7	58.4	62.1	61.7	243.9	61.0	58.7	58.5	53.0	231.2	30.7	26.9	30.9	34.5	123.0
Fab 30	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
Fab8A	0.9	1.3	1.4	1.4	5.0	1.2	1.2	1.2	1.2	4.8	1.1	1.1	1.0	1.0	4.2
Fab8B	9.7	11.9	10.7	7.7	40.0	8.4	7.7	9.1	13.0	38.2	19.5	25.9	31.8	41.4	118.5
SONY	0.6	0.4	0.2	0.1	1.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
0.13u Fdry #1 -	0.0	0.0	0.0	0.0	0.0	6.0	3.8	5.9	1.1	16.9	0.0	0.0	0.0	0.0	0.0
LATTICE	6.8	6.7	6.7	6.7	27.1	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0
Fab 25	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 14/15	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0
LEGERITY	19.4	19.7	20.5	20.6	80.1	21.1	23.4	24.9	25.4	94.8	25.9	26.9	27.9	28.7	109.5
FAB 14/15	19.4	19.7	20.5	20.6	80.1	21.1	23.4	24.9	25.4	94.8	25.9	26.9	27.9	28.7	109.5
MEMORY	102.4	105.8	115.7	129.7	453.6	128.5	138.6	153.8	175.5	596.3	192.0	209.8	232.4	244.9	879.0
FASL 4	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.5	0.5	5.5	16.0	28.0	37.8	87.3
FAB 14/15	3.9	3.0	3.9	3.8	14.6	2.8	2.9	3.0	2.9	11.5	2.8	2.8	2.8	2.8	11.2
FASL - GMD	8.7	10.7	14.3	24.2	57.9	27.0	25.8	27.8	36.0	116.6	38.5	41.2	44.1	46.7	170.5
FASL - IWATE	17.0	16.3	16.6	17.6	67.5	15.1	14.5	13.4	14.0	57.0	17.1	17.9	18.9	18.9	72.6
FASL 1	45.0	44.7	47.3	48.0	185.0	48.0	45.6	45.6	45.6	184.8	39.0	41.2	44.8	44.9	169.8
FASL 2	27.9	31.1	33.6	35.6	128.1	35.7	36.9	37.7	40.4	150.6	43.0	42.3	42.1	41.6	168.9
FASL 3	0.0	0.0	0.0	0.5	0.5	0.0	12.9	26.3	36.2	75.4	46.2	48.5	51.9	52.3	198.8
TOTAL FAB	239.2	249.5	267.8	276.1	1032.6	288.4	302.2	323.3	342.9	1256.8	346.1	368.4	402.6	428.8	1545.8

**THREE-YEAR PLAN
 WAFER FABRICATION GROUP COMMITS (K, 8")
 BY DIVISION BY FAB**

PRODUCT LINE	<u>1Q01</u>	<u>2Q01</u>	<u>3Q01</u>	<u>4Q01</u>	<u>2001</u>	<u>1Q02</u>	<u>2Q02</u>	<u>3Q02</u>	<u>4Q02</u>	<u>2002</u>	<u>1Q03</u>	<u>2Q03</u>	<u>3Q03</u>	<u>4Q03</u>	<u>2003</u>
AMD	85.9	88.1	96.8	94.6	365.3	109.1	111.0	114.5	108.6	443.1	89.7	87.0	92.1	95.8	364.6
0.13u Fdry #1 - (BULK)	0.0	0.0	0.0	0.0	0.0	6.0	3.8	5.9	1.1	16.9	0.0	0.0	0.0	0.0	0.0
Fab 25	59.9	55.5	58.4	57.8	231.6	57.1	54.3	53.8	48.5	213.7	26.8	23.1	27.1	30.9	107.9
Fab 30	26.0	32.6	38.4	36.8	133.8	46.0	52.8	54.7	58.9	212.5	62.9	63.9	65.0	64.9	256.7
EPD	7.2	9.6	10.1	9.8	36.7	9.4	9.8	9.9	9.4	38.6	8.8	8.9	8.7	8.5	35.0
EPSON	0.1	0.1	0.1	0.1	0.5	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
FAB 14/15	4.2	5.2	4.9	4.3	18.6	3.9	3.7	3.3	2.9	13.8	2.8	2.8	2.6	2.4	10.7
Fab 25	1.8	2.9	3.7	3.9	12.3	3.9	4.4	4.7	4.5	17.5	3.9	3.8	3.8	3.6	15.1
Fab8A	0.1	0.3	0.4	0.4	1.2	0.3	0.3	0.3	0.3	1.3	0.3	0.3	0.3	0.3	1.3
Fab8B	0.3	0.6	0.8	1.0	2.7	1.3	1.4	1.6	1.7	5.9	1.8	2.0	2.0	2.2	8.0
SONY	0.6	0.4	0.2	0.1	1.3	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
LATTICE	6.8	6.7	6.7	6.7	27.1	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0
FAB 14/15	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0	6.7	6.7	6.7	6.7	27.0
Fab 25	0.1	0.0	0.0	0.0	0.1	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0
LEGERITY	19.4	19.7	20.5	20.6	80.1	21.1	23.4	24.9	25.4	94.8	25.9	26.9	27.9	28.7	109.5
FAB 14/15	19.4	19.7	20.5	20.6	80.1	21.1	23.4	24.9	25.4	94.8	25.9	26.9	27.9	28.7	109.5
NPD	8.1	8.3	8.1	8.0	32.5	6.5	6.5	6.3	6.3	25.6	6.1	6.1	6.3	6.3	24.9
FAB 14/15	7.4	7.2	7.0	6.8	28.4	5.4	5.4	5.0	5.0	20.7	4.4	4.4	4.1	4.1	16.9
Fab8A	0.7	1.0	1.0	1.1	3.9	0.9	0.9	0.9	0.9	3.5	0.7	0.7	0.7	0.7	2.9
Fab8B	0.0	0.0	0.0	0.0	0.0	0.1	0.1	0.4	0.4	0.9	0.9	0.9	1.4	1.4	4.7
TSMC	0.0	0.1	0.1	0.1	0.3	0.1	0.1	0.1	0.1	0.5	0.1	0.1	0.1	0.1	0.4
NVD	102.4	105.8	115.7	129.7	453.6	128.5	138.6	153.8	175.5	596.3	192.0	209.8	232.4	244.9	879.0
FAB 14/15	3.9	3.0	3.9	3.8	14.6	2.8	2.9	3.0	2.9	11.5	2.8	2.8	2.8	2.8	11.2
FASL - GMD	8.7	10.7	14.3	24.2	57.9	27.0	25.8	27.8	36.0	116.6	38.5	41.2	44.1	46.7	170.5
FASL - IWATE	17.0	16.3	16.6	17.6	67.5	15.1	14.5	13.4	14.0	57.0	17.1	17.9	18.9	18.9	72.6
FASL 1	45.0	44.7	47.3	48.0	185.0	48.0	45.6	45.6	45.6	184.8	39.0	41.2	44.8	44.9	169.8
FASL 2	27.9	31.1	33.6	35.6	128.1	35.7	36.9	37.7	40.4	150.6	43.0	42.3	42.1	41.6	168.9
FASL 3	0.0	0.0	0.0	0.5	0.5	0.0	12.9	26.3	36.2	75.4	46.2	48.5	51.9	52.3	198.8
FASL 4	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.0	0.5	0.5	5.5	16.0	28.0	37.8	87.3
PPD	9.4	11.3	9.9	6.7	37.2	7.1	6.2	7.2	11.0	31.4	16.7	22.9	28.4	37.8	105.8
Fab8B	9.4	11.3	9.9	6.7	37.2	7.1	6.2	7.2	11.0	31.4	16.7	22.9	28.4	37.8	105.8
TOTAL FAB	239.2	249.5	267.8	276.1	1032.6	288.4	302.2	323.3	342.9	1256.8	346.1	368.4	402.6	428.8	1545.8